Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6832	mram magnetic adj (ram random adj access adj memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:04
L2	6842	mram magnetic adj (ram random adj access adj memory) mrram pfram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:04
L3	6846	mram (magnetic magneto)adj (ram random adj access adj memory) mrram pfram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:04
L4	6938	mram (magnet$4 ferromagnet$4 ferrimagnet$4) adj (ram random adj access adj memory) mrram pfram	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:05
L5	170081	silicon near2 (carbide carbon) sic sinc sinoc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:08
L6	224	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:09
L7	4646	etch$4 with 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24
L8	20	7 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24
L9	2	8 and (@ad < "20020116")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24
L10	8608	etch$4 same 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24

L11	41	10 and 4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24
L12	11	11 and (@ad < "20020116")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24
L13	9	12 not 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:24
L14	6160	((438/694) or (438/702) or (438/703) or (438/725) or (438/734)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/20 18:33
S96	1	"6719634".pn.	USPAT	OR	OFF	2005/06/20 15:21
S97	1	"6797628".pn.	USPAT	OR	OFF	2005/06/20 16:13
S98	15	(("6599814") or ("6569257") or ("6387551") or ("6340435") or ("6373950") or ("6064081") or ("5965463") or ("0546617") or ("5335256") or ("5269258") or ("5135885") or ("5116462") or ("5070027") or ("4861533")).PN.	USPAT; USOCR	OR	OFF	2005/06/20 16:14
S99	139630	silicon adj (carbide carbon) sic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:22
S100	2057286	semiconductor ic integrated adj circuit vlsi ulsi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:17
S101	39290	S99 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:16
S102	2057286	semiconductor ic integrated adj circuit vlsi ulsi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:17

S10 3	39290	S99 and S102	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:20
S10 4	6832	mram magnetic adj (ram random adj access adj memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:21
S10 5	0	S98 and S104	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:22
S10 6	11	S98 and S100	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:23
S10 7	142926	silicon adj (carbide carbon) sic sinc sinoc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:23
S10 8	11	S98 and S107	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:24
S10 9	170081	silicon near2 (carbide carbon) sic sinc sinoc	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 18:05
S11 0	11	S98 and S109	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/20 16:24